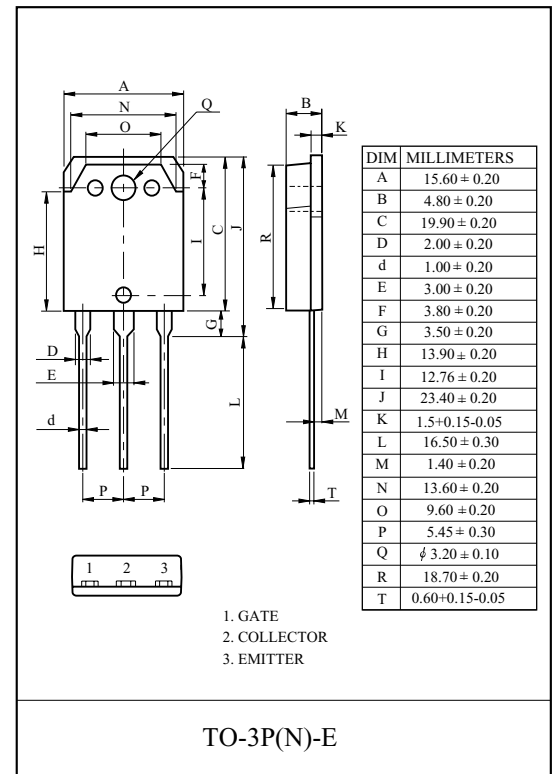


General Description

KEC NPT IGBTs offer lowest losses and highest energy efficiency for application such as IH (induction heating), UPS, General inverter and other soft switching applications.

FEATURES

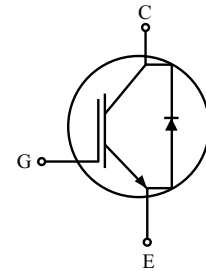
- High speed switching
- Higher system efficiency
- Soft current turn-off waveforms
- Square RBSOA using NPT technology



MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collector Current	@T _C =25 °C	I_C	40	A
	@T _C =100 °C		25	A
Pulsed Collector Current		I_{CM}^*	75	A
Diode Continuous Forward Current	@T _C =100 °C	I_F	25	A
Diode Maximum Forward Current		I_{FM}	110	A
Maximum Power Dissipation	@T _C =25 °C	P_D	300	W
	@T _C =100 °C		120	W
Maximum Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55 to +150	°C

*Repetitive rating : Pulse width limited by max. junction temperature



THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	$R_{\theta JC}$	0.4	°C/W
Thermal Resistance, Junction to Case (DIODE)	$R_{\theta JC}$	1.2	°C/W

KGGH25N120NDA

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Static							
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=500\mu A$	1200	-	-	V	
Collector Cut-off Current	I_{CES}	$V_{GE}=0V, V_{CE}=1200V$	-	-	250	μA	
Gate Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 100	nA	
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=25mA$	5.0	6.0	7.0	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=25A$	-	2.5	3.0	V	
Dynamic							
Total Gate Charge	Q_g	$V_{CC}=600V, V_{GE}=15V, I_C=25A$	-	200	-	nC	
Gate-Emitter Charge	Q_{ge}		-	20	-	nC	
Gate-Collector Charge	Q_{gc}		-	100	-	nC	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC}=600V, I_C=25A, V_{GE}=15V, R_G=10\ \Omega$ Inductive Load, $T_C=25\ ^\circ C$	-	60	-	ns	
Rise Time	t_r		-	60	-	ns	
Turn-Off Delay Time	$t_{d(off)}$		-	200	-	ns	
Fall Time	t_f		-	50	-	ns	
Turn-On Switching Loss	E_{on}		-	2.0	-	mJ	
Turn-Off Switching Loss	E_{off}		-	1.0	-	mJ	
Total Switching Loss	E_{is}		-	3.0	-	mJ	
Turn-On Delay Time	$t_{d(on)}$		$V_{CC}=600V, I_C=25A, V_{GE}=15V, R_G=10\ \Omega$ Inductive Load, $T_C=125\ ^\circ C$	-	60	-	ns
Rise Time	t_r			-	60	-	ns
Turn-Off Delay Time	$t_{d(off)}$	-		200	-	ns	
Fall Time	t_f	-		70	-	ns	
Turn-On Switching Loss	E_{on}	-		3.0	-	mJ	
Turn-Off Switching Loss	E_{off}	-		1.5	-	mJ	
Total Gate Charge	E_{is}	-		4.5	-	mJ	
Input Capacitance	C_{ies}	$V_{CE}=30V, V_{GE}=0V, f=1MHz$		-	2200	-	pF
Output Capacitance	C_{oes}			-	200	-	pF
Reverse Transfer Capacitance	C_{res}		-	100	-	pF	

ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Diode Forward Voltage	V_F	$I_F=10A$	$T_C=25\ ^\circ C$	-	1.8	2.5	V
			$T_C=125\ ^\circ C$	-	1.7	-	
Diode Reverse Recovery Time	t_{rr}	$I_F=10A$	$T_C=25\ ^\circ C$	-	250	350	ns
			$T_C=125\ ^\circ C$	-	300	-	
Diode Peak Reverse Recovery Current	I_{rr}	$di/dt=200A/\mu s$	$T_C=25\ ^\circ C$	-	5	10	A
			$T_C=125\ ^\circ C$	-	10	-	

KGH25N120NDA

Fig 1. Typical Output Characteristics

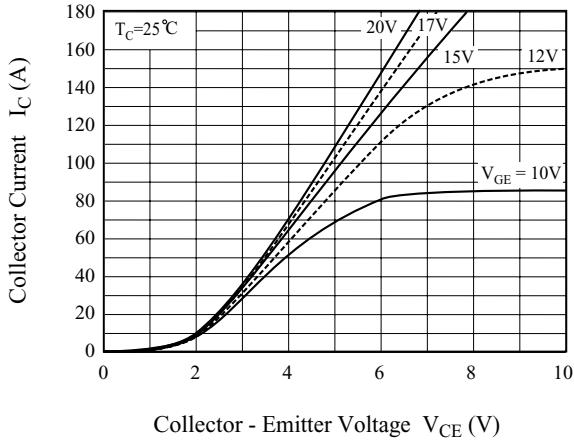


Fig 2. Typical Saturation Voltage Characteristics

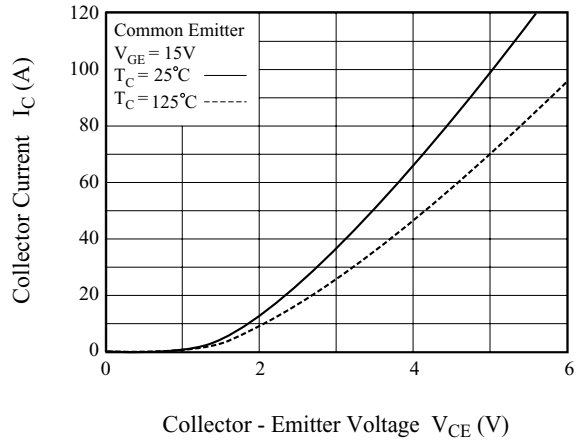


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

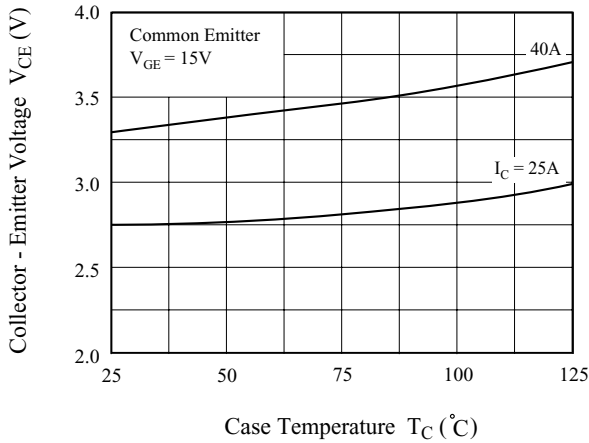


Fig 4. Saturation Voltage vs. V_{GE}

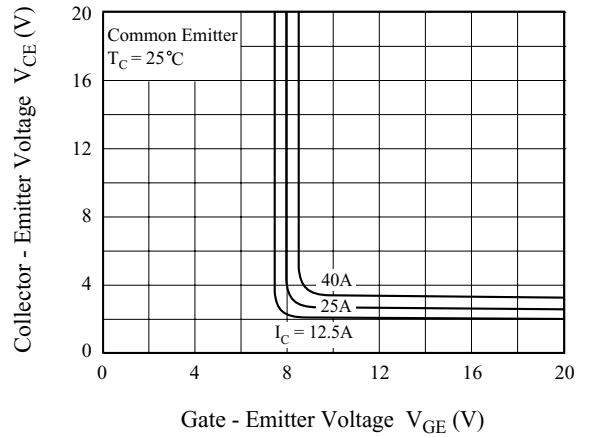


Fig 5. Saturation Voltage vs. V_{GE}

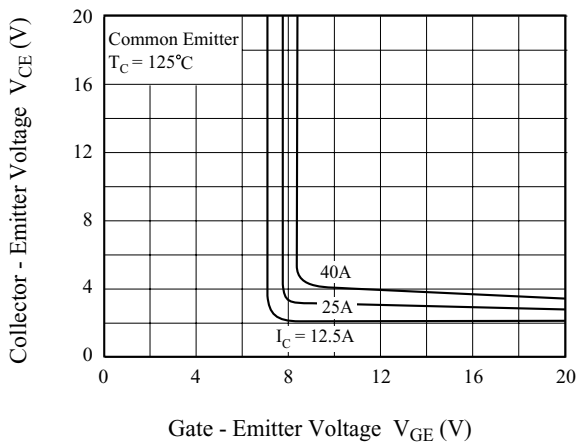
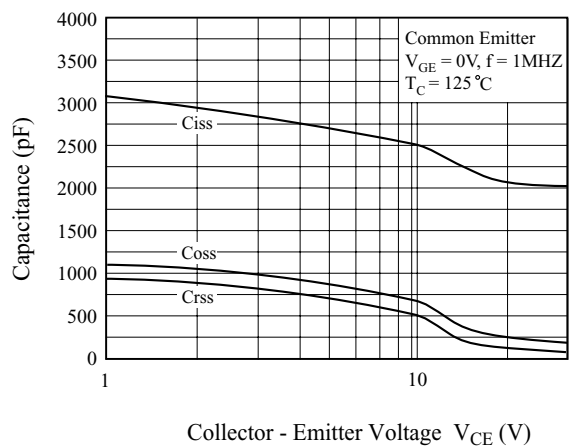


Fig 6. Capacitance Characteristics



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Fig 7. Turn-On Characteristics vs. Gate Resistance

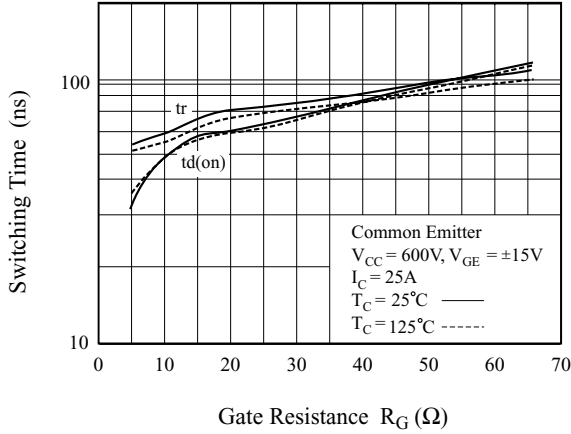


Fig 8. Turn-On Characteristics vs. Gate Resistance

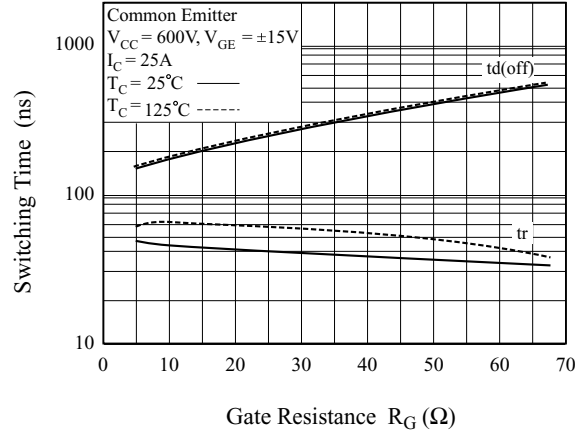


Fig 9. Switching Loss vs. Gate Resistance

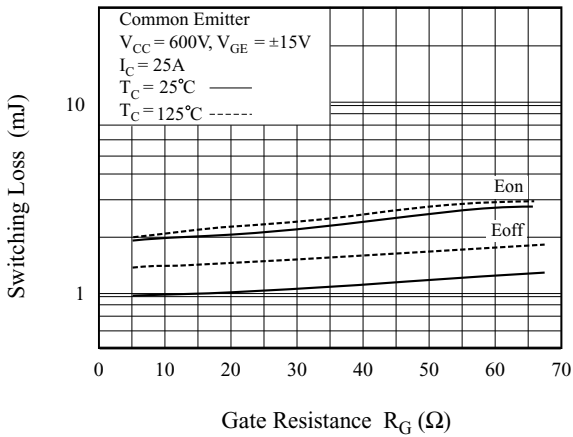


Fig 10. Turn-On Characteristics vs. Collector Current

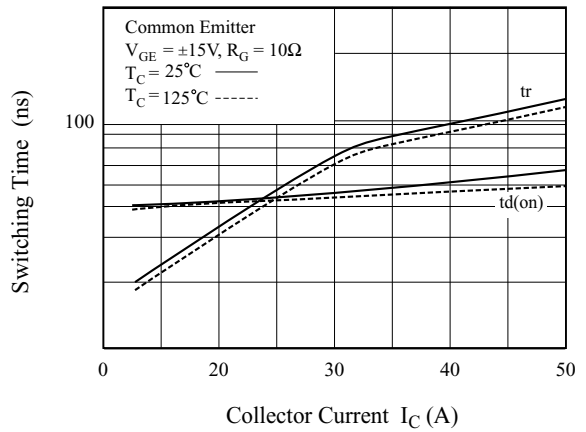


Fig 11. Turn-Off Characteristics vs. Collector Current

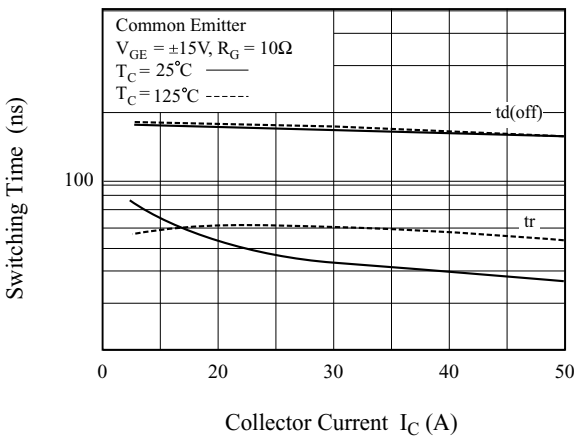
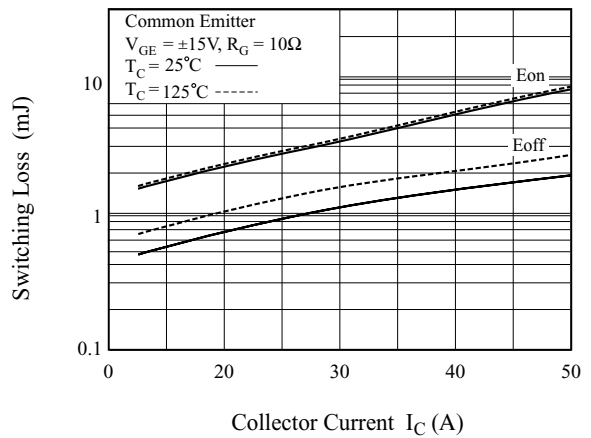


Fig 12. Switching Loss vs. Collector Current



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Fig 13. Gate Charge Characteristics

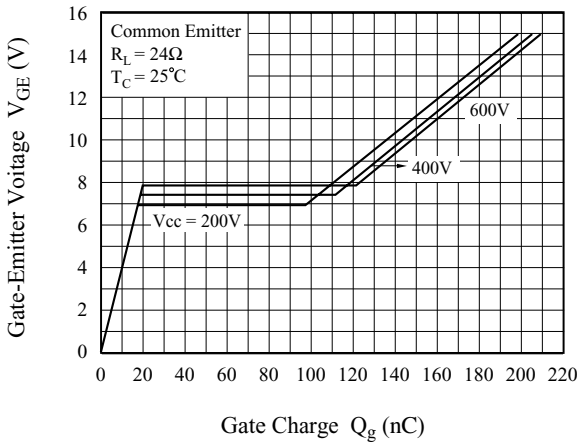


Fig 14. SOA Characteristics

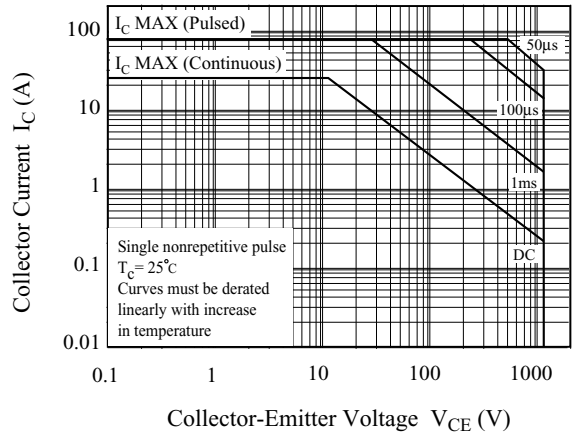


Fig 15. Turn-Off SOA

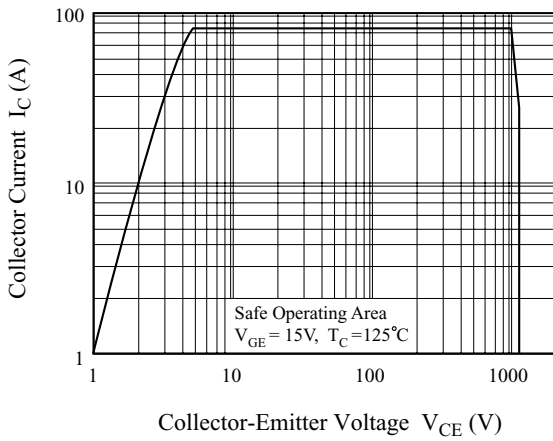
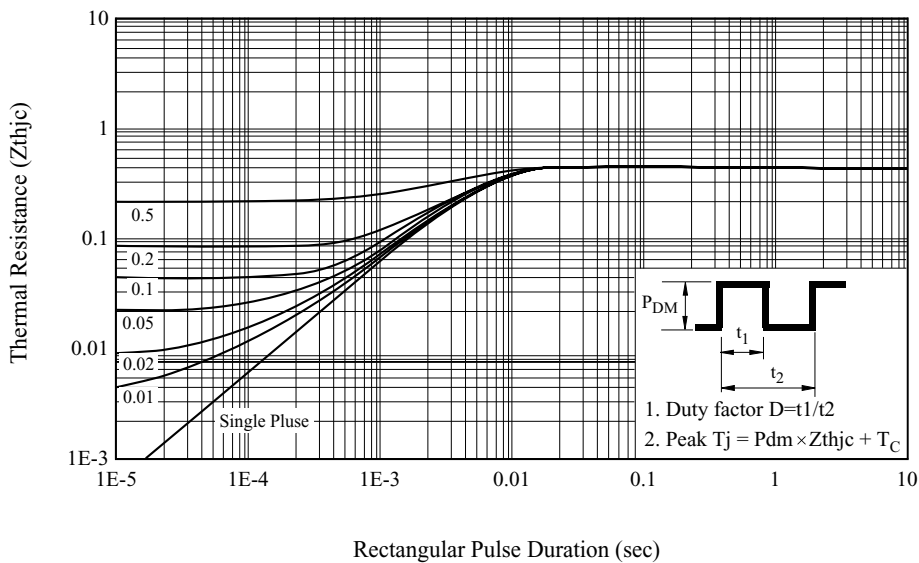


Fig 16. Transient Thermal Impedance of IGBT



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Fig 17. Forward Characteristics

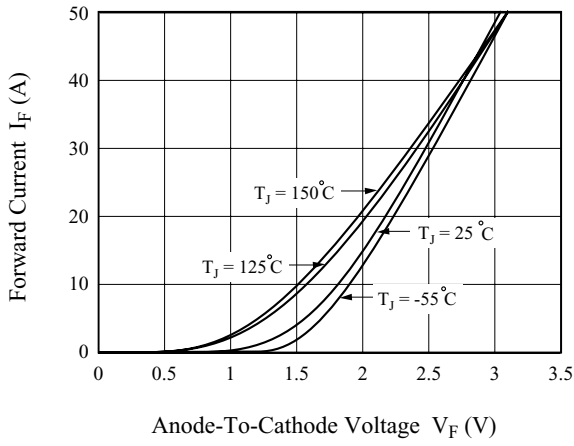


Fig 18. Reverse Recovery Current

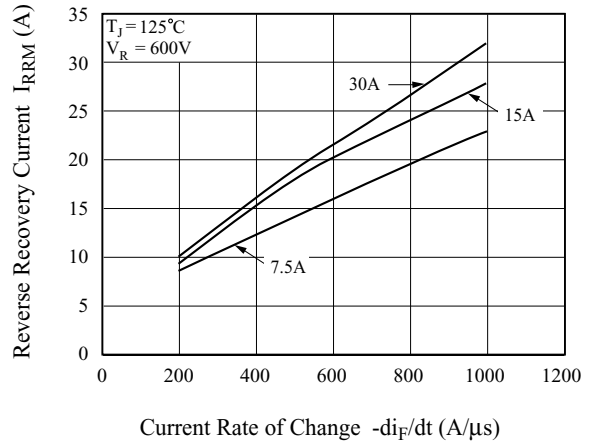


Fig 19. Maximum Average Forward Current vs. Case Temperature

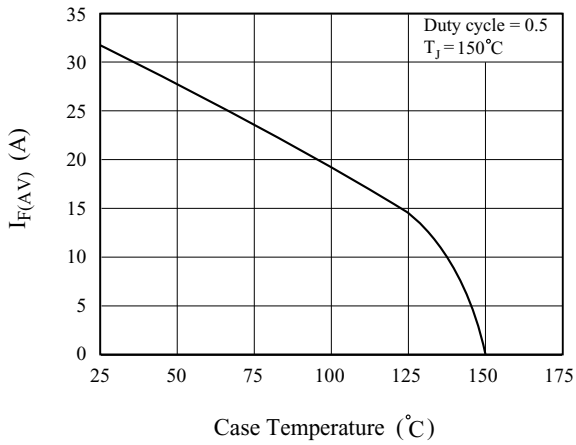


Fig 20. Reverse Recovery Time

